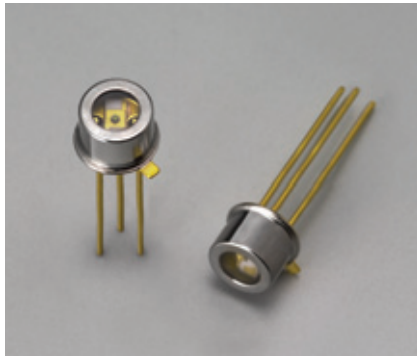


InGaAs PIN photodiodes

G8376 series

25-05826



Standard type

InGaAs PIN photodiodes are NIR (near infrared) detectors that feature high-speed response and low noise.

Features

- Low noise, low dark current
- Low terminal capacitance
- 3-pin TO-18 package

Applications

- NIR (near infrared) photometry
- Optical communication

Specifications

Parameter	Symbol	G8376-03	G8376-05	Unit
Window material	-	Borosilicate glass with anti-reflective coating (optimized for 1.55 μm peak)		-
Package	-	TO-18		-
Active area	-	φ0.3	φ0.5	mm

Absolute maximum ratings

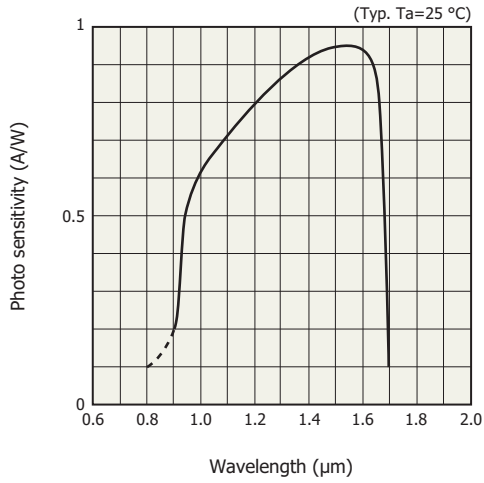
Parameter	Symbol	G8376-03	G8376-05	Unit
Reverse voltage	V _R	20		V
Operating temperature	T _{opr}	-40 to +85		°C
Storage temperature	T _{stg}	-55 to +125		°C

Electrical and optical characteristics (T_a=25 °C)

Parameter	Symbol	Condition	G8376-03			G8376-05			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Spectral response range	λ		-	0.9 to 1.7	-	-	0.9 to 1.7	-	μm
Peak sensitivity wavelength	λ _p		-	1.55	-	-	1.55	-	μm
Photo sensitivity	S	λ=1.3 μm	0.8	0.9	-	0.8	0.9	-	A/W
		λ=λ _p	0.85	0.95	-	0.85	0.95	-	
Dark current	I _D	V _R =5 V	-	0.3	1.5	-	0.5	2.5	nA
Cut-off frequency	f _c	V _R =5 V, R _L =50 Ω, -3 dB	-	400	-	-	200	-	MHz
Terminal capacitance	C _t	V _R =5 V, f=1 MHz	-	5	-	-	12	-	pF
Shunt resistance	R _{sh}	V _R =10 mV	-	1000	-	-	300	-	MΩ
D*	-	λ=λ _p	-	5 × 10 ¹²	-	-	5 × 10 ¹²	-	cm·Hz ^{1/2} /W
Noise equivalent power	NEP	λ=λ _p	-	4 × 10 ⁻¹⁵	-	-	8 × 10 ⁻¹⁵	-	W/Hz ^{1/2}

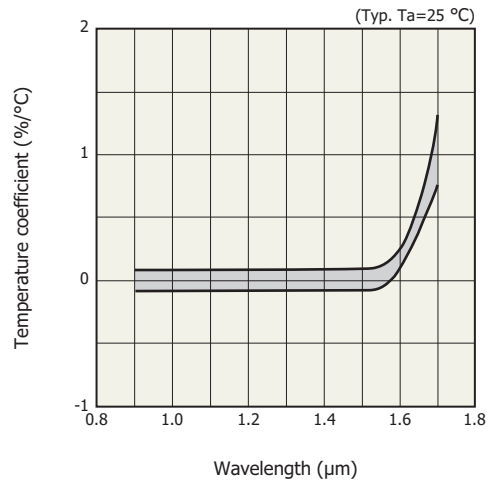
G8376 series may be damaged by electrostatic discharge. Be carefull when using G8376 series.

Spectral response



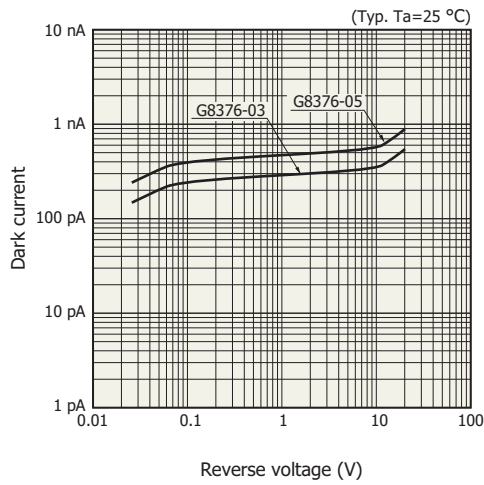
KIRDB0002EB

Photo sensitivity temperature characteristic



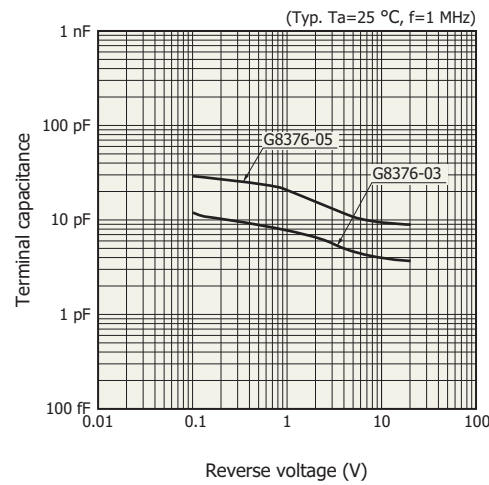
KIRDB0042EA

Dark current vs. reverse voltage



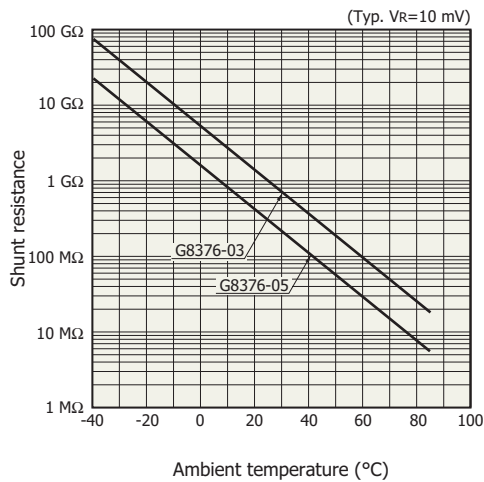
KIRDB0249EB

Terminal capacitance vs. reverse voltage



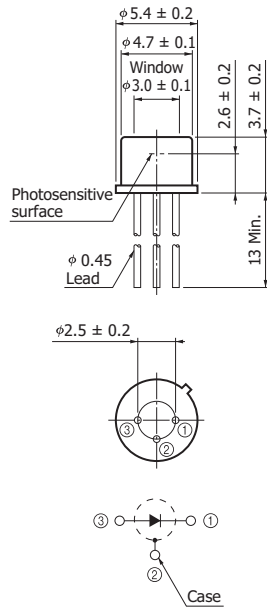
KIRDB0250EB

Shunt resistance vs. ambient temperature



KIRDB0251EB

Dimensional outline (unit: mm)



KIRDA0150EB

Information furnished by HAMAMATSU is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions. Specifications are subject to change without notice. No patent rights are granted to any of the circuits described herein. ©2008 Hamamatsu Photonics K.K.

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